# ECE 340 Lecture 4 Semiconductor Electronics 

Spring 2022<br>10:00-10:50am<br>Professor Umberto Ravaioli<br>Department of Electrical and Computer Engineering<br>2062 ECE Building

## Today's Discussion

- Crystal States
- Types of Bonding
- Insulators, Metals, and Semiconductors
- Band structure
- Direct and Indirect Band Gap
- Electrons and Holes


## Crystal Bonding

- Each atom shares bonds with 4 other atoms.
- Silicon bonds are covalent, but compound semiconductors have a mix of ionic and covalent bonds.


When silicon atoms COMBINE to form a crystal the $s$ - and $p$ - orbitals HYBRIDIZE to form so-called $s p^{3}$ ORBITALS that are mixtures of the $s$ - and $p$-orbitals.

s-ORBITAL

p-ORBITAL

$s p^{3}$-ORBITAL

## Crystal Bonding

Bring atoms together, the wavefunctions begin to overlap.


## Energy Band Formation

IN A SINGLE ATOM ELECTRONS ARE TRAPPED IN A POTENTIAL WELL


WHEN MANY ATOMS COMBINE AND FORM A CRYSTAL THE ATOMIC POTENTIALS OVERLAP GIVING RISE TO A PERIODIC VARIATION

## Energy Band Formation

surface


## Energy Band Formation



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## Gedanken Experiment

Imagine you start with $a \gg$ and then shrink down to exact size


## Energy Bands Formation

Silicon $-1 s^{2} 2 s^{2} 2 p^{6} 3 s^{2} 3 p^{2}$
Relative spacing of atoms

Atomic \#
$Z=14$
$\mathrm{N}=$ atoms in crystal


From Solid State Electronic Devices, Sixth Edition, by Ben G. Streetman and Sanjay Kumar Banerjee.

## ATOMS ARE FAR AWAY FROM EACH OTHER AND DO NOT INTERACT

Silicon $-1 s^{2} 2 s^{2} 2 p^{6} 3 s^{2} 3 p^{2}$
Relative spacing of atoms

Atomic \#
$Z=14$
$\mathrm{N}=$ atoms in crystal


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## ATOMS START INTERACTING - BONDING \& ANTIBONDING STATES START FORMING

## Relative spacing ff atoms

Silicon $-1 s^{2} 2 s^{2} 2 p^{6} 3 s^{2} 3 p^{2} \quad \mathbf{2}$ states each level

Atomic \#
$Z=14$
$\mathrm{N}=$ atoms in crystal


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## STRONGER INTERACTION - sp³ ORBITAL HYBRIDIZATION STARTS

## Relative spacing of atoms

Silicon $-1 s^{2} 2 s^{2} 2 p^{6} 3 s^{2} 3 p^{2}$
2 states each level
Atomic \#
$Z=14$
$\mathrm{N}=$ atoms in crystal


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## STABLE CRYSTAL CONFIGURATION REACHED - COVALENT BONDING VALENCE AND CONDUCTION BANDS WITH BAND GAP ARE FORMED

Relative spacing of atoms
Silicon $-1 s^{2} 2 s^{2} 2 p^{6} 3 s^{2} 3 p^{2} \quad 2$ states each level

Atomic \#
$Z=14$
$\mathrm{N}=$ atoms in crystal


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## Energy Bands Formation

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## Energy Band Formation

surface

space coordinate

## Periodic Table of the Elements

|  | 1 | 2 | 3 | 4 | 5 |  | 6 | 7 | 8 | 9 | 10 | 11 | 12 | \||| | IV | V | VI | 17 | 18 |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 1 | $\stackrel{1}{\mathrm{H}}$ <br> $\underset{\substack{\text { Hydrosen } \\ 1 \\ 1}}{ }$ |  | C | Solid |  |  |  |  | Metals |  |  | Nonme | etals |  | $\sqrt{ }$ |  |  |  |  |
| 2 | $\underbrace{\mathrm{Li}}_{\substack{\text { Litium } \\ \text { Lisi }}}$ | Be <br> $\substack{\text { Beplilium } \\ \text { a. } 0.12182}$ |  | Liquid <br> Gas |  |  | $\begin{aligned} & \stackrel{\rightharpoonup}{\hat{\hat{N}}} \\ & \underline{\underline{\omega}} \\ & \stackrel{\rightharpoonup}{\bar{\omega}} \end{aligned}$ |  | Lanthanoids |  |  |  | $\begin{aligned} & \text { z } \\ & \frac{\square}{0} \\ & \stackrel{0}{0} \\ & 0 \end{aligned}$ | B |  |  |  |  | 10 <br> Ne <br> Nen <br> 20. <br> 187 |
| 3 | ${ }^{11} \mathrm{Na}$ <br> Sadium <br> 223989298 |  |  | Unknown |  |  | $\stackrel{\stackrel{\omega}{\omega}}{\omega}$ |  | Actinoids |  | $\frac{\stackrel{\rightharpoonup}{0}}{0}$ |  |  | 13 AI Aluminium 28.9815396 |  | $\begin{aligned} & 15 \\ & \mathbf{P} \end{aligned}$ | $\begin{aligned} & 16 \\ & \mathrm{~S} \\ & \text { Sutur } \\ & \hline 220085 \\ & \hline \end{aligned}$ | $\begin{aligned} & 17 \\ & \mathrm{Cl} \\ & \text { Clatione } \\ & 35453 \end{aligned}$ | $\begin{aligned} & 18 \\ & \mathrm{Ar} \\ & \text { An } \\ & \text { angn } \\ & \hline 1948 \end{aligned}$ |
| 4 | $\stackrel{\substack{\text { Potassium } \\ 390.093 \\ \hline}}{19}$ |  |  |  | $\left\lvert\, \begin{aligned} & 23 \\ & \mathbf{V} \\ & \mathbf{V} \text { Vandum } \\ & 50.9415 \end{aligned}\right.$ |  |  |  |  |  | 28 Ni <br> Noxel <br> 58.6934 |  |  |  |  |  |  |  | 36 <br> Kr <br> Kypuen <br> 83.398 |
| 5 |  |  | $\square$ |  | $\begin{array}{\|l\|} \hline 41 \\ \text { Nb } \\ \text { Nobium } \\ \text { S20038 } \end{array}$ |  |  |  | $\square$ |  |  |  |  | $\begin{aligned} & 49 \\ & \text { In } \\ & \text { Indium } \\ & \text { In } 14.818 \end{aligned}$ |  |  | 52 <br> Te <br> Tetrium <br> 127.00 | $\square$ | 54 <br> Xe <br> Xenen <br> 131233 |
| 6 |  | 56 <br> Ba <br> 137.327 | 57-71 |  |  | $74$ | W <br> Hungsten 833.84 |  |  |  | $\begin{aligned} & \hline 78 \\ & \mathrm{Pt} \\ & \text { Plation } \\ & \text { Paso } \\ & \hline \end{aligned}$ |  |  | $\begin{aligned} & 81 \\ & \mathrm{TI} \\ & \hline \end{aligned}$ |  | 83 Bi Bismuth 208.98040 | 84 Po Po Poanium 2030.324 | 85 <br> At <br> Astatine (209.9871) | 86 Rn Raston (220.016) |
| 7 | 87 Fr Francum (223) |  | 89-103 | $\square$ | 105 Db Dubhum (282) |  | $\begin{aligned} & 106 \\ & \text { Sg } \begin{array}{l} \text { Sastosium } \end{array} . \end{aligned}$ |  |  |  | $\begin{aligned} & 110 \\ & \text { Ds } \\ & \text { Des } \begin{array}{l} \text { anseatm } \\ \text { (271) } \end{array} \end{aligned}$ |  |  | $\begin{array}{\|l\|l} 113 \\ \text { Uut } \\ \text { Ununtium } \\ \text { (244) } \end{array}$ | $\qquad$ |  |  | 117 Uus unreatam |  |

For elements with no stable isotopes, the mass number of the isotope with the longest half-life is in parentheses.

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## Ionic Bonding



For elements with no stable isotopes, the mass number of the isotope with the longest half-life is in parentheses.

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## Ionic Bonding


ionic bonding
electron transferred from Na to Cl

## Metallic Bonding



For elements with no stable isotopes, the mass number of the isotope with the longest half-life is in parentheses.

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## Metallic Bonding


metallic bonding ions surrounded by free electrons

## Covalent Bonding

|  | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 | 12 |  | IV | V | VI | 17 | 18 |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 1 | $\underset{\substack{1 \\ H \\ \text { Hydrosen } \\ 1.00794}}{ }$ |  | C | Solid |  |  |  | Metals |  |  | Nonme | tals |  |  |  |  |  | $\begin{aligned} & 2 \\ & \mathrm{He} \\ & \substack{\text { Hetum } \\ 4.00202} \end{aligned}$ |
| 2 | $\begin{aligned} & 3 \\ & \mathbf{L i} \\ & \hline \text { Litum } \\ & 0.941 \end{aligned}$ |  | $\begin{aligned} & \hline \mathrm{Hg} \\ & \hline \mathrm{H} \\ & \hline \end{aligned}$ | Liquid <br> Gas |  | $\begin{aligned} & \text { 릋 } \\ & \underline{\underline{\text { en }}} \end{aligned}$ |  | Lanthanoids |  | $\begin{aligned} & 0 \\ & 0 \\ & 0 \\ & \vdots \\ & 0 \end{aligned}$ |  | $\begin{aligned} & \text { Z } \\ & \frac{0}{\bar{\theta}} \\ & 0 \\ & \hline 0 \end{aligned}$ |  |  | $\underset{\substack{\text { NTtrgen } \\ \text { 14.0087 }}}{\mathrm{N}}$ |  |  | $\begin{aligned} & 10 \\ & \mathrm{Ne} \\ & \text { Neon } \\ & \text { 20.1797 } \end{aligned}$ |
| 3 | 11 <br> Na <br> $\substack{\text { sadum } \\ 223979928}$ |  | Rf | Unknown |  | $\frac{\stackrel{\rightharpoonup}{6}}{\omega}$ |  | Actinoids |  | $\frac{\stackrel{N}{\omega}}{}$ |  | $\begin{aligned} & \stackrel{\rightharpoonup}{0} \\ & \stackrel{y}{*} \end{aligned}$ | $\begin{aligned} & 13 \\ & \mathrm{Al} \end{aligned}$ | $\begin{array}{\|l\|} \hline 14 \\ \mathrm{Si} \\ \text { siten } \\ 2800055 \\ \hline \end{array}$ |  | $\begin{aligned} & 16 \\ & \text { S } \\ & \text { Sulur } \\ & 322085 \end{aligned}$ | $\begin{array}{\|c} \hline 17 \\ \mathrm{Cl} \\ \text { Clomene } \\ 354.433 \\ \hline \end{array}$ | $\begin{aligned} & 18 \\ & \mathrm{Ar} \\ & \substack{\text { Argn } \\ 39.948} \end{aligned}$ |
| 4 |  | $\begin{aligned} & 20 \\ & \mathrm{Ca} \end{aligned}$ $\begin{aligned} & \text { Cabioum } \\ & \text { 40, } \end{aligned}$ |  |  | $\begin{aligned} & 23 \\ & \mathbf{V} \\ & \begin{array}{l} \text { vanadum } \\ 50.9415 \end{array} \\ & \hline \end{aligned}$ |  |  |  |  | 28 Ni <br> Nickel <br> 58.6934 |  |  |  |  | As <br> Assenic | $\begin{aligned} & 34 \\ & \mathrm{Se} \\ & \text { Se } \end{aligned}$ $78.90$ |  |  |
| 5 |  |  | $\begin{aligned} & 39 \\ & \mathbf{Y} \\ & \text { Ytrium } \\ & 88,5055 \end{aligned}$ |  |  |  |  |  |  |  |  |  | 49 In Intum 114.818 | $\begin{array}{\|l} 50 \\ \mathrm{Sn} \\ \text { Tin } \\ \text { in } \\ \hline \end{array}$ | $\square$ |  |  |  |
| 6 |  |  | 57-71 |  |  |  | 75 <br> Re <br> Ren <br> 1880207 |  |  | $\begin{aligned} & \hline 78 \\ & \text { Pt } \\ & \begin{array}{l} \text { Platinum } \\ 195.084 \end{array} \\ & \hline \end{aligned}$ |  |  | $\begin{aligned} & 81 \\ & \text { TI } \\ & \text { Trative } \\ & 204.383 \end{aligned}$ | $\begin{aligned} & 82 \\ & \mathrm{~Pb} \\ & \hline \begin{array}{l} \text { Pe8 } \\ 207.2 \end{array} \end{aligned}$ | $\square$ |  |  |  |
| 7 |  |  | 89-103 | $\square$ | $\begin{aligned} & 105 \\ & \mathrm{Db} \\ & \text { Dubum } \\ & \text { Oubrium } \end{aligned}$ | 106 <br> Sg <br> Segosorium <br> (288) | 107 Bh Borhium (284) |  |  | $\begin{aligned} & 110 \\ & \text { Ds } \\ & \text { Dessation } \\ & \text { (271) } \end{aligned}$ |  |  |  |  |  |  | 117 <br> Uus <br> Unvestam | $\begin{aligned} & 118 \\ & \text { Uuo } \\ & \text { Unurasur } \\ & \text { Unest } \end{aligned}$ |

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## Covalent Bonding



## Behavioral Classification

insulator
empty
$\square$


 $r_{1}+6+6+6+4+4+4+4+6$



filled

## semiconductor



$$
\mathrm{T}=0 \mathrm{~K}
$$

## Phase Space

Dynamics of electrons is studied in a generalized system of coordinates:


The kinetic energy state of the particle is given by a function

$$
E=f\left(k_{x}, k_{y}, k_{z}\right)
$$

This is usually known as "band structure".
As we have seen, energy in a crystal is a multi-valued function, so the band structure has many branches.

## Classical particle

For a classical particle in free space there is only a single value of energy for each set of momentum coordinates.

$$
E=\frac{1}{2} m v^{2}
$$

Momentum is defined as

$$
p=m v \rightarrow E=\frac{p^{2}}{2 m}
$$

This is a simple parabolic relation


## Quantum mechanical particle

For a quantum mechanical particle described by the Schrödinger equation inside a crystal, we define a new "crystal" momentum

$$
\langle p\rangle=\hbar k
$$

Here $\boldsymbol{k}$ is the wave number of the wave describing the particle quantum-mechanically and for convenience it is used most often as momentum coordinate.

## Quantum mechanical particle

We model the crystal as a new kind of "free space" where the particles obey a new energy-momentum relationship given by the band structure, containing the effects of the periodic atomic potentials.

Therefore, what we study is not an electron "particle" as in an isolated atom or in vacuum, but an electron "quasiparticle" which obeys special dynamic laws as dictated by the specific crystal in which it moves.

## Simple examples of band structure

| Lowest energy |
| :--- |
| solution in the |
| conduction band |

Highest energy solution in the valence band

(a) Direct

(b) Indirect

## Simple examples of band structure

Often it is sufficient to analyze conduction band behavior only in the region close to the minimum of the lowest energy branch, called a "valley".

In many cases the $\mathrm{E}(\mathrm{k})$ relations in the valleys are with good approximation parabolic

(a) Direct

(b) Indirect

Often it is sufficient to analyze valence band behavior only in the region close to the maximum of the highest energy branch, also called a "valley".

## Simple examples of band structure



At finite temperature, electrons have the probability to acquire sufficient thermal energy to be excited to the conduction band.

An empty state is left behind, which essentially behaves like a positive "quasi-particle" (hole) moving when neighboring valence electron jump into that empty space leaving another one behind
(a) Direct

## Direct or indirect?



## Direct or indirect?



## Direct or indirect?



## Semiconductor Material Properties

|  |  | $\begin{gathered} E_{g} \\ (\mathrm{eV}) \\ \hline \end{gathered}$ | $\begin{gathered} \mu_{n} \\ \left(\mathrm{~cm}^{2} / \mathrm{V}-\mathrm{s}\right) \end{gathered}$ | $\begin{gathered} \mu_{\rho} \\ \left(\mathrm{cm}^{2} / \mathrm{V}-\mathrm{s}\right) \end{gathered}$ | $\begin{gathered} m_{n}^{*} / m_{0} \\ \left(m_{1}, m_{t}\right) \end{gathered}$ | $\begin{gathered} m_{p}^{*} / m_{o} \\ \left(m_{l h}, m_{h h}\right) \end{gathered}$ | $a(\AA)$ | $\epsilon_{r}$ | Density $\left(\mathrm{g} / \mathrm{cm}^{3}\right)$ | Melting point $\left({ }^{\circ} \mathrm{C}\right)$ | C (diamond)$E_{g}=5.5 e V$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Si | (i/D) | 1.11 | 1350 | 480 | 0.98, 0.19 | $0.16,0.49$ | 5.43 | 11.8 | 2.33 | 1415 |  |
| Ge | (i/D) | 0.67 | 3900 | 1900 | 1.64, 0.082 | 0.04, 0.28 | 5.65 | 16 | 5.32 | 936 |  |
| $\mathrm{SiC}(\alpha)$ | (i/W) | 2.86 | 500 | - | 0.6 | 1.0 | 3.08 | 10.2 | 3.21 | 2830 | $\mathrm{SiO}_{2}$ |
| AlP | (i/Z) | 2.45 | 80 | - | - | 0.2, 0.63 | 5.46 | 9.8 | 2.40 | 2000 | $E_{g}=9.0 \mathrm{eV}$ |
| AlAs | (i/Z) | 2.16 | 1200 | 420 | 2.0 | $0.15,0.76$ | 5.66 | 10.9 | 3.60 | 1740 |  |
| AlSb | (i/Z) | 1.6 | 200 | 300 | 0.12 | 0.98 | 6.14 | 11 | 4.26 | 1080 |  |
| GaP | (i/Z) | 2.26 | 300 | 150 | 1.12, 0.22 | 0.14, 0.79 | 5.45 | 11.1 | 4.13 | 1467 |  |
| GaAs | (d/Z) | 1.43 | 8500 | 400 | 0.067 | 0.074, 0.50 | 5.65 | 13.2 | 5.31 | 1238 |  |
| GaN | ( $d / Z, W$ ) | 3.4 | 380 | - | 0.19 | 0.60 | 4.5 | 12.2 | 6.1 | 2530 |  |
| GaSb | (d/Z) | 0.7 | 5000 | 1000 | 0.042 | 0.06, 0.23 | 6.09 | 15.7 | 5.61 | 712 |  |
| $\ln P$ | (d/Z) | 1.35 | 4000 | 100 | 0.077 | 0.089, 0.85 | 5.87 | 12.4 | 4.79 | 1070 |  |
| $\ln A s$ | (d/Z) | 0.36 | 22600 | 200 | 0.023 | 0.025, 0.41 | 6.06 | 14.6 | 5.67 | 943 |  |
| lnSb | (d/Z) | 0.18 | $10^{5}$ | 1700 | 0.014 | 0.015, 0.40 | 6.48 | 17.7 | 5.78 | 525 |  |
| ZnS | $(d / Z, W)$ | 3.6 | 180 | 10 | 0.28 | - | 5.409 | 8.9 | 4.09 | 1650* |  |
| ZnSe | (d/Z) | 2.7 | 600 | 28 | 0.14 | 0.60 | 5.671 | 9.2 | 5.65 | $1100^{*}$ |  |
| ZnTe | (d/Z) | 2.25 | 530 | 100 | 0.18 | 0.65 | 6.101 | 10.4 | 5.51 | 1238* |  |
| CdS | ( $d / W, Z$ ) | 2.42 | 250 | 15 | 0.21 | 0.80 | 4.137 | 8.9 | 4.82 | 1475 |  |
| CdSe | ( $d / \mathrm{W}$ ) | 1.73 | 800 | - | 0.13 | 0.45 | 4.30 | 10.2 | 5.81 | 1258 |  |
| CdTe | (d/Z) | 1.58 | 1050 | 100 | 0.10 | 0.37 | 6.482 | 10.2 | 6.20 | 1098 |  |
| PbS | (i/H) | 0.37 | 575 | 200 | 0.22 | 0.29 | 5.936 | 17.0 | 7.6 | 1119 |  |
| PbSe | (i/H) | 0.27 | 1500 | 1500 | - | - | 6.147 | 23.6 | 8.73 | 1081 |  |
| PbTe | (i/H) | 0.29 | 6000 | 4000 | 0.17 | 0.20 | 6.452 | 30 | 8.16 | 925 |  |

